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Steckel et al.

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(54) **QUANTUM DOT LED AND OLED
INTEGRATION FOR HIGH EFFICIENCY
DISPLAYS**

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(2013.01); *H01L 51/0013* (2013.01); *H01L*

51/5016 (2013.01); *H01L 2251/5369* (2013.01)

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(58) **Field of Classification Search**

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See application file for complete search history.

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2, 2016.

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H01L 51/50 (2006.01)

H01L 51/52 (2006.01)

H01L 51/00 (2006.01)

(57) **ABSTRACT**

Displays including hybrid pixels including an OLED sub-
pixel and QD-LED subpixel are described. In an embod-
iment, OLED and QD-LED stacks are integrated into the
same pixel with multiple common layers shared by the
OLED and QD-LED stacks.

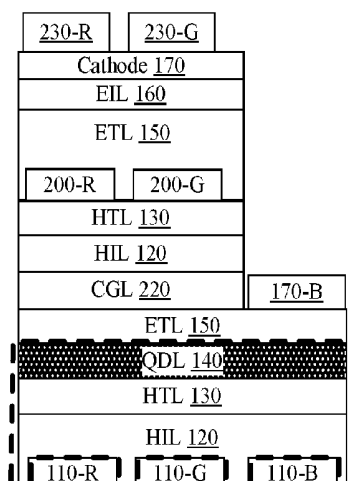
(52) **U.S. Cl.**

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(2013.01); *H01L 51/502* (2013.01); *H01L*

51/5044 (2013.01); *H01L 51/5072* (2013.01);

15 Claims, 7 Drawing Sheets



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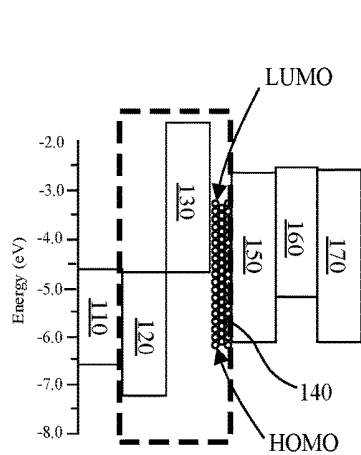


FIG. 1

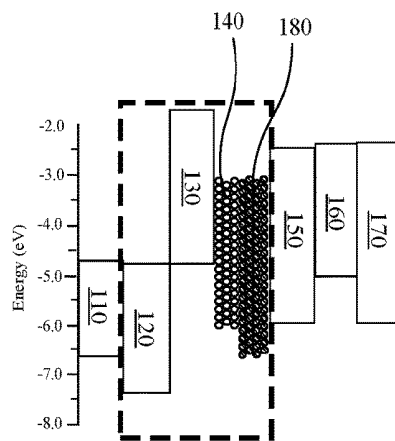


FIG. 2

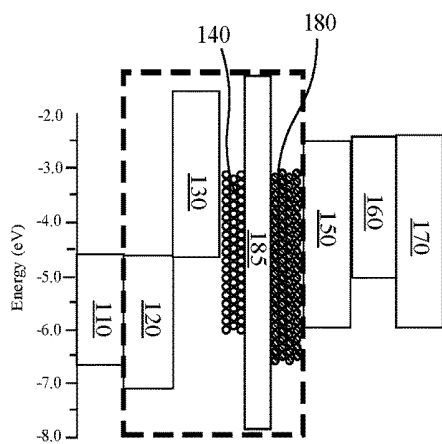


FIG. 3

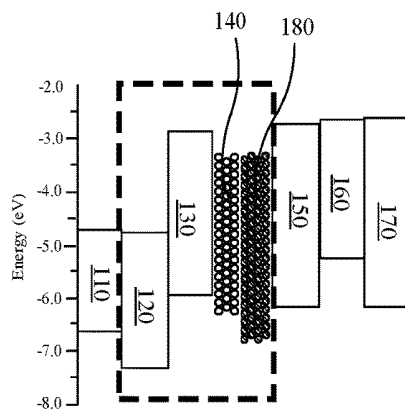


FIG. 4

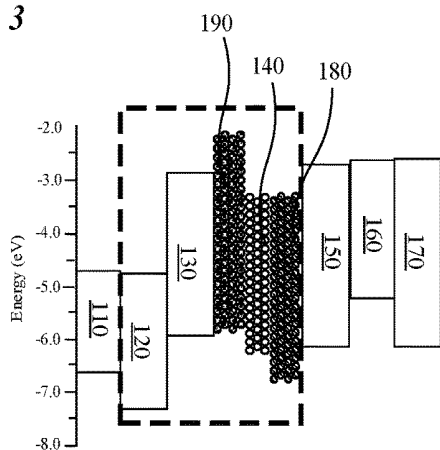


FIG. 5

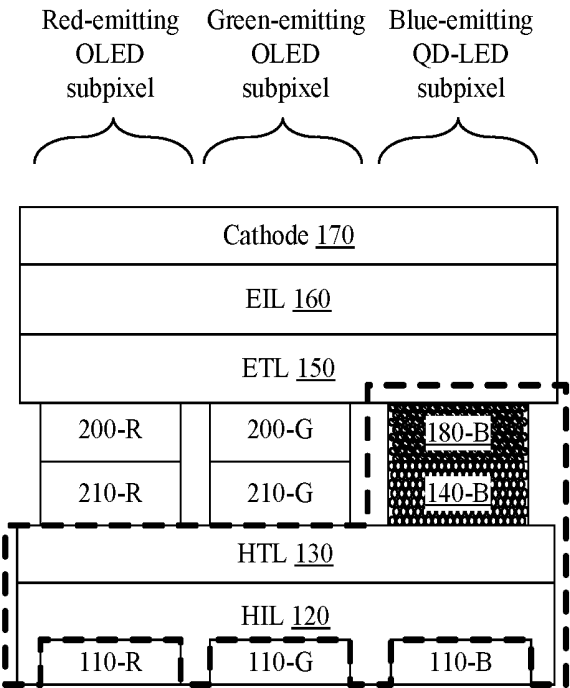


FIG. 6

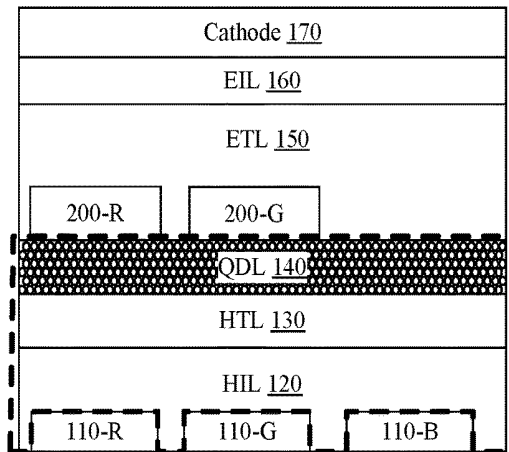


FIG. 7

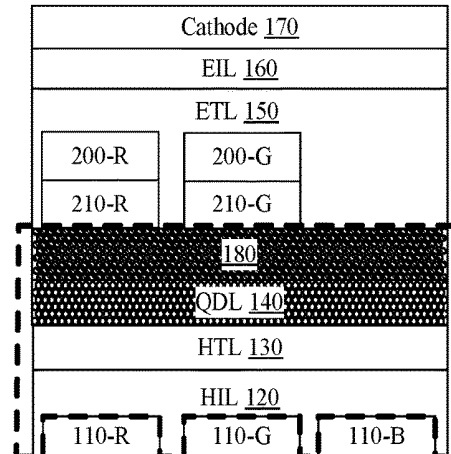


FIG. 8

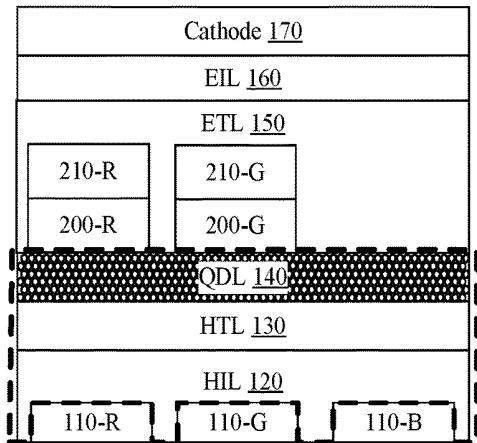


FIG. 9

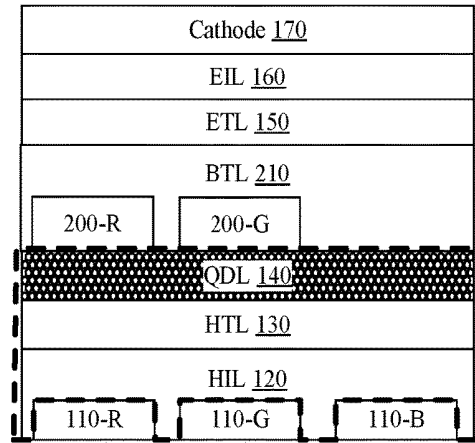


FIG. 10

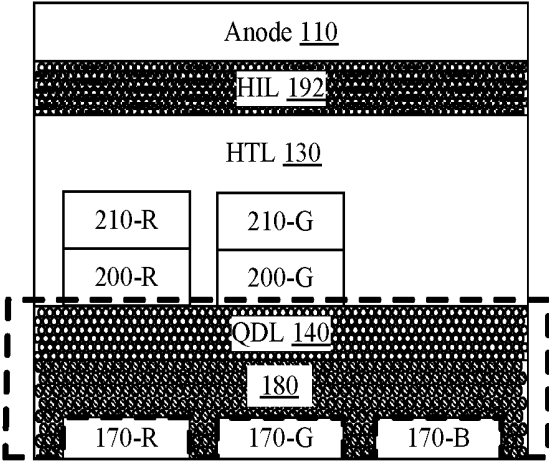


FIG. 11

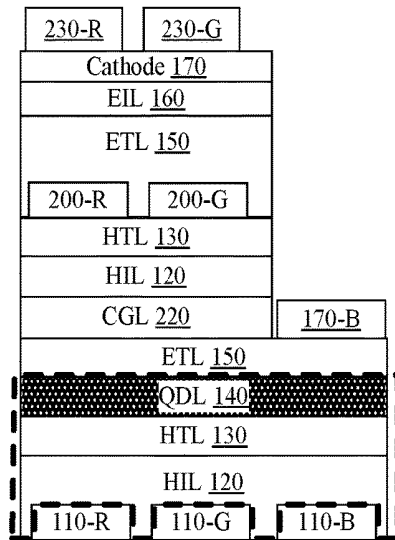


FIG. 12

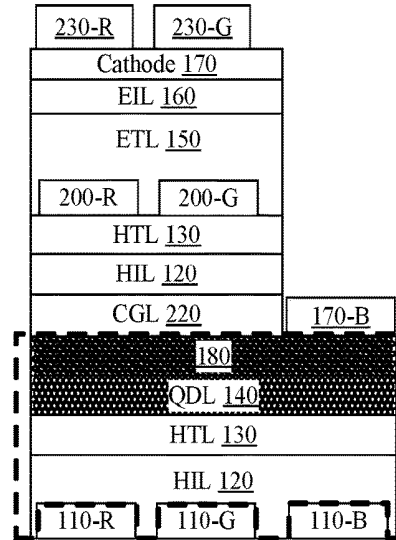


FIG. 13

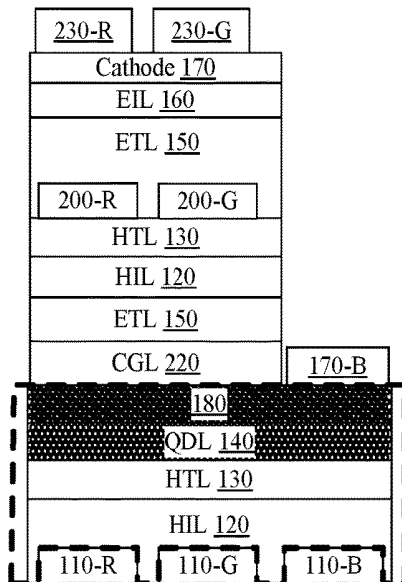


FIG. 14

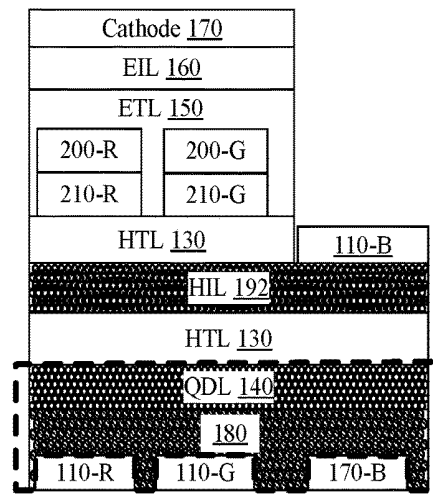


FIG. 15

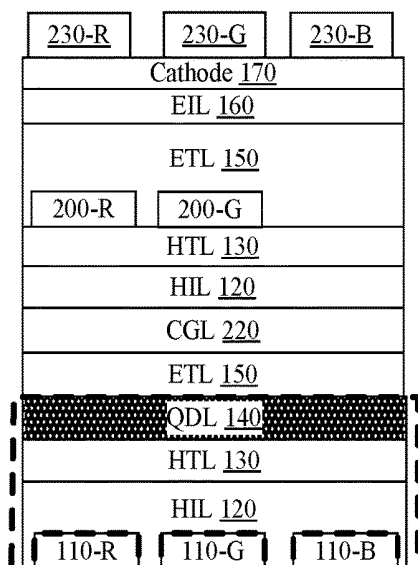


FIG. 16

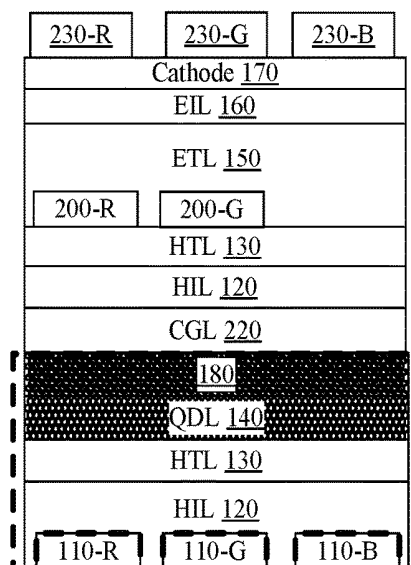


FIG. 17

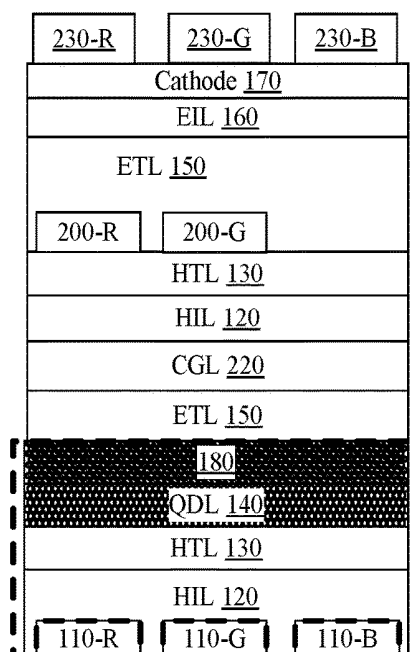


FIG. 18

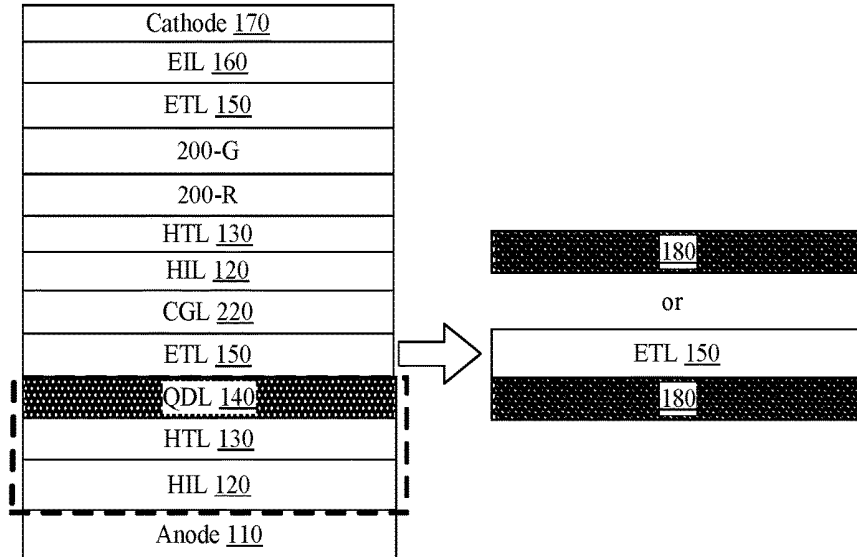


FIG. 19

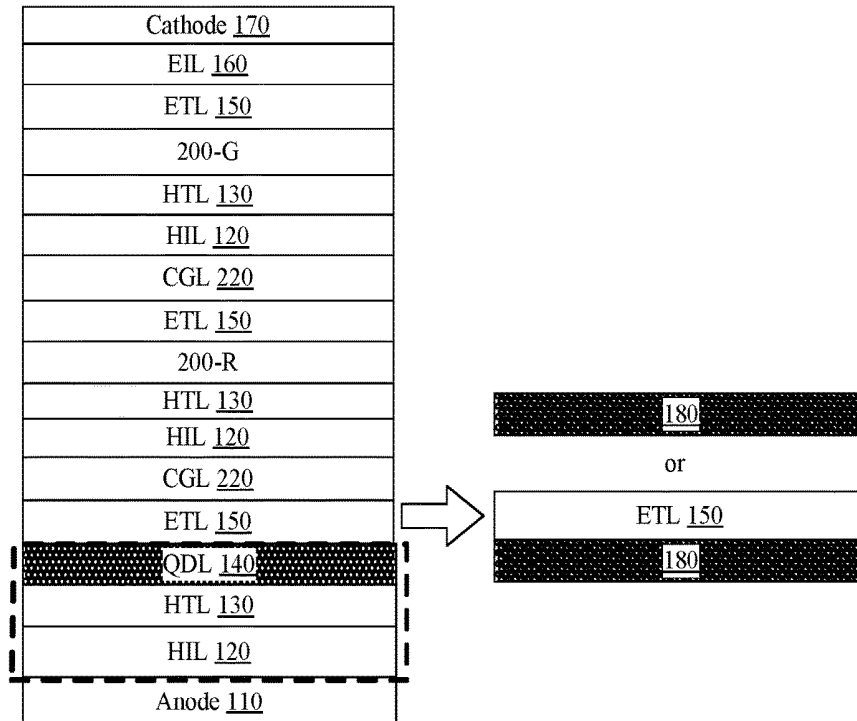


FIG. 20

QUANTUM DOT LED AND OLED INTEGRATION FOR HIGH EFFICIENCY DISPLAYS

This application is a divisional of U.S. patent application Ser. No. 15/244,906 filed on Aug. 23, 2016 now U.S. Pat. No. 10,192,932, issued Jan. 29, 2019, which claims the priority of U.S. Provisional Application No. 62/290,423 filed on Feb. 2, 2016, both of which are incorporated herein by reference.

BACKGROUND

Field

Embodiments described herein relate to display systems. More particularly, embodiments relate to display systems with hybrid emissive light emitting diodes (LEDs).

Background Information

State of the art displays for phones, tablets, computers and televisions utilize glass substrates with thin-film transistors (TFT) to control transmission of backlight through pixels based on liquid crystals. More recently emissive displays such as those based on organic light emitting diodes (OLED) have been introduced because they can have a faster response time, and be more power efficient, allowing each pixel to be turned off completely when displaying black or dark colors, and be compatible with plastic substrates. Even more recently, quantum dot light emitting diodes (QD-LEDs) have been introduced as an alternative display technology, potentially being more power efficient than OLEDs.

SUMMARY

Display systems and hybrid pixel arrangements are described. In an embodiment, a display includes a hybrid pixel with an OLED subpixel and a QD-LED subpixel. A common hole transport layer is in the OLED subpixel and the QD-LED subpixel. A quantum dot layer is over the common hole transport layer in the QD-LED subpixel, and an organic emission layer that includes a phosphorescent material is over the common hole transport layer in the OLED subpixel. A common electron transport layer is over the quantum dot layer in the QD-LED subpixel, and over the organic emission layer in the OLED subpixel. A common top electrode layer is over the common electron transport layer in the OLED subpixel and the QD-LED subpixel.

In an embodiment, a method of forming a display includes forming a common hole transport layer over a display backplane in using a first solution technique, where the common hole transport layer is formed over the display backplane in an OLED subpixel and a QD-LED subpixel. A quantum dot layer is then formed over the common hole transport layer in the QD-LED subpixel. An organic emission layer including a phosphorescent material may then be evaporated over the common hole transport layer in the OLED subpixel. A common electron transport layer may be evaporated over the quantum dot layer in the QD-LED subpixel, and over the organic emission layer in the OLED subpixel. A common top electrode layer may then be formed over the common electron transport layer in the OLED subpixel and the QD-LED subpixel.

In an embodiment, a display includes a tandem hybrid pixel including an OLED subpixel and a QD-LED subpixel. A common hole transport layer is in the OLED subpixel and the QD-LED subpixel. A common quantum dot layer is over the common hole transport layer in the QD-LED subpixel and in the OLED subpixel. A semi-common charge genera-

tion layer is over the common quantum dot layer in the OLED subpixel. A first cathode is over the common quantum dot layer in the QD-LED subpixel. A semi-common hole transport layer is over the semi-common charge generation layer in the OLED subpixel. An organic emission layer is over the semi-common hole transport layer in the OLED subpixel. A semi-common electron transport layer is over the organic emission layer in the OLED subpixel, and a semi-common second cathode is over the semi-common electron transport layer in the OLED subpixel. In an embodiment, a common nanoparticle electron transport layer including metal-oxide nanoparticles is over the common quantum dot layer in the QD-LED subpixel and in the OLED subpixel, the semi-common charge generation layer is over the common nanoparticle electron transport layer in the OLED subpixel, and the first cathode is over the common nanoparticle electron transport layer in the QD-LED subpixel.

In an embodiment, a display includes a tandem hybrid pixel including an OLED subpixel and a QD-LED subpixel. A common hole transport layer is in the OLED subpixel and the QD-LED subpixel. A common quantum dot layer is over the common hole transport layer in the QD-LED subpixel and in the OLED subpixel. A common charge generation layer is over the common quantum dot layer in the OLED subpixel and in the QD-LED subpixel, and a common hole transport layer is over the common charge generation layer in the OLED subpixel and in the QD-LED subpixel. An organic emission layer is over the common hole transport layer in the OLED subpixel. A common electron transport layer is over the common hole transport layer in the OLED subpixel and in the QD-LED subpixel, and the common electron transport layer is additionally over the organic emission layer in the OLED subpixel. A common cathode is over the common electron transport layer in the OLED subpixel and in the QD-LED subpixel. In an embodiment, a common nanoparticle electron transport layer including metal-oxide nanoparticles is over the common quantum dot layer in the QD-LED subpixel and in the OLED subpixel, and the common charge generation layer is over the common nanoparticle electron transport layer in the OLED subpixel and in the QD-LED subpixel.

In an embodiment a display with a tandem QD-LED and OLED tandem stack includes a common anode, a common hole transport layer over the common anode, a common quantum dot layer over the common hole transport layer, a common charge generation layer over the common quantum dot layer, a common hole transport layer over the common charge generation layer, a common organic emission layer over the common hole transport layer, a common electron transport layer over the common organic emission layer, and a common cathode over the common electron transport layer. In an embodiment, the tandem QD-LED and OLED tandem stack further includes a second common organic emission layer between the common organic emission layer and the common electron transport layer. In an embodiment, the tandem QD-LED and OLED tandem stack further includes a second common electron transport layer over the common organic emission layer, a second charge generation layer over the second common electron transport layer, and a second hole transport layer over the second charge generation layer, where the second common organic emission layer is over the second hole transport layer.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is an energy diagram of the layers in a QD-LED stack in accordance with an embodiment.

FIG. 2 is an energy diagram of the layers in a QD-LED stack including a metal oxide nanoparticle electron transport layer in accordance with an embodiment.

FIG. 3 is an energy diagram of the layers in a QD-LED stack including an insulating layer between a quantum dot layer and a metal oxide nanoparticle electron transport layer in accordance with an embodiment.

FIG. 4 is an energy diagram of the layers in a QD-LED stack including a hole transport layer with modified energy levels in accordance with an embodiment.

FIG. 5 is an energy diagram of the layers in a QD-LED stack including a metal oxide nanoparticle hole transport layer in accordance with an embodiment.

FIG. 6 is a schematic cross-sectional side view illustration of a hybrid pixel including a patterned quantum dot layer in accordance with an embodiment.

FIGS. 7-10 are schematic cross-sectional side view illustrations of hybrid pixels including a common quantum dot layer in accordance with embodiments.

FIG. 11 is a schematic cross-sectional side view illustration of an inverted hybrid pixel including a common quantum dot layer in accordance with an embodiment.

FIGS. 12-18 are schematic cross-sectional side view illustrations of hybrid pixels including tandem structure stacks in accordance with embodiments.

FIGS. 19-20 are schematic cross-sectional side view illustrations blended emission tandem structure stacks in accordance with embodiments.

DETAILED DESCRIPTION

Embodiments describe display systems with hybrid pixels. In an embodiment, a display includes a hybrid pixel including an OLED subpixel and a QD-LED subpixel. A common hole transport layer is in the OLED subpixel and the QD-LED subpixel with commonly shared layers. A quantum dot (QD) layer is over the common hole transport layer in the QD-LED subpixel. In some embodiments, the QD layer is a common layer over the common hole transport layer in the OLED subpixel and the QD-LED subpixel. An organic emission layer is over the common hole transport layer in the OLED subpixel. In some embodiments the organic emission layer is over the common QD layer in the OLED subpixel. A common electron transport layer is over the QD layer in the QD-LED subpixel and over the organic emission layer in the OLED subpixel. A common top electrode layer is over the common electron transport layer in the OLED subpixel and the QD-LED subpixel.

While power efficiency for OLEDs is a potential benefit of OLED displays, conventional fluorescent OLEDs are known to have a maximum internal quantum efficiency (IQE) of around 25%. Phosphorescent OLED systems may be more efficient, and can have IQE values approaching 100%. As such, it may be advantageous to employ phosphorescent OLED materials in displays. Red and green phosphorescent OLED devices have high efficiencies, saturated colors, and acceptable lifetimes. For blue phosphorescent materials, however, available materials tend to have unacceptably short lifetime, unsaturated colors, or both. As such, there is a need to improve the blue emitter system in an OLED display, while maintaining the acceptable performance of red and green phosphorescent materials.

In an embodiment, a hybrid pixel includes a blue-emitting QD-LED pixel and one or more emitting OLED subpixels, such as a green-emitting OLED subpixel and a red-emitting OLED subpixel in a RGB hybrid pixel layout. In a specific embodiment, the red OLED subpixel and green OLED

subpixel include phosphorescent OLED materials. It is to be appreciated that an RGB hybrid pixel layout is exemplary, and embodiments are not so limited. Other exemplary pixel arrangements include red-green-blue-yellow-cyan (RB-GYC), red-green-blue-white (RGBW), or other sub-pixel matrix schemes where the pixels have a different number of sub-pixels.

In various embodiments, description is made with reference to figures. However, certain embodiments may be practiced without one or more of these specific details, or in combination with other known methods and configurations. In the following description, numerous specific details are set forth, such as specific configurations, dimensions and processes, etc., in order to provide a thorough understanding of the embodiments. In other instances, well-known display processes and manufacturing techniques have not been described in particular detail in order to not unnecessarily obscure the embodiments. Reference throughout this specification to "one embodiment" means that a particular feature, structure, configuration, or characteristic described in connection with the embodiment is included in at least one embodiment. Thus, the appearances of the phrase "in one embodiment" in various places throughout this specification are not necessarily referring to the same embodiment. Furthermore, the particular features, structures, configurations, or characteristics may be combined in any suitable manner in one or more embodiments.

The terms "above", "over", "to", "between", and "on" as used herein may refer to a relative position of one layer with respect to other layers. One layer "above", "over", or "on" another layer may be directly in contact with the other layer or may have one or more intervening layers. One layer "between" layers may be directly in contact with the layers or may have one or more intervening layers.

Referring now to FIGS. 1-5 various cross-sectional side view illustrations are provided of QD-LED stacks in accordance with embodiments. In the particular embodiments illustrated (including those illustrated in FIGS. 6-9), a dashed outline is provided around a group of layers that may be fabricated using solution-based processing. These groupings are exemplary, and intended to visually illustrate the potential impact of solution-based processing, however, the embodiments are not limited to solution-based processing. In one aspect, increasing the ratio of solution-based processed layers can potentially lead to increased performance and reduced cost of fabrication. For example, solution-based processing may have a reduced time of production compared to evaporation techniques. Solution-based processing of layers may potentially reduce the number of processing steps, and increase yield. For example, solution-based process may negate concerns with exposing evaporated species to air, solvent, etc. In some embodiments, solution-based processing is implemented only prior to the formation of an organic layer by thermal evaporation.

FIG. 1 is an energy diagram of the layers in a QD-LED stack in accordance with an embodiment. As shown, the QD-LED stack may include an anode 110, a hole injection layer (HIL) 120 on/over the anode 110, a hole transport layer (HTL) 130 on/over the HIL 120, a QD layer 140 on/over the HTL 130, an electron transport layer (ETL) 150 on/over the QD layer 140, an electron injection layer (EIL) 160 on/over the ETL 150, and a cathode 170 on/over the EIL 160. As described and illustrated herein a layer on/over another layer may be directly on (in contact) with the other layer or may have one or more intervening layers. In operation, a voltage is applied across the QD-LED stack such that the anode is positive with respect to the cathode. Current flows through

the QD-LED stack from the cathode to anode, as electrons are injected from the cathode **170** into the lowest unoccupied molecular orbital (LUMO) of the QD layer **140**, while electrons are withdrawn toward the anode **110** from the highest occupied molecular orbital (HOMO) of the QD layer **140** (alternately described as hole injection into the HOMO of the QD layer **140**). Recombination of electrons and holes in the QD layer **140** is accompanied by emission of radiation, the frequency of which dependent upon the band gap of the QDs, or the difference in energy (eV) between the HOMO and LUMO. It is to be appreciated that the particular energy levels illustrated in FIGS. 1-5 are exemplary, and that the energy levels are variable. Accordingly, the particular energy levels illustrated are provided for illustrative purposes only, and embodiments are not limited to the specific energy levels illustrated.

Still referring to FIG. 1, an anode **110** is formed on a display substrate, such as a TFT substrate, or substrate including redistribution lines. Anode **110** may be formed of a variety of electrically conductive materials. In an embodiment, anode **110** is formed of indium-tin-oxide (ITO). For example, ITO may be formed by sputtering or thermal evaporation. In an embodiment, an array of anodes **110** is sputtered onto a display substrate through a mask, such as a fine metal mask, with a separate anode **110** formed in each subpixel.

As shown, a HIL **120** is formed on the anode **110**. In accordance with embodiments, the HIL **120** may be a common layer shared by multiple subpixels within a pixel, and may be a common layer across multiple pixels. The HIL **120** facilitates the injection of positive charge (holes) from the anode **110** into the HTL **130**. The HIL **120** may be formed of materials such as conductive polymer-based materials (e.g. poly thiophenes, poly anilines), combination of arylamine based hole transport host and electron accepting dopant (e.g. charge transfer salts), strongly electron accepting small organic molecules, metal oxides. The HIL **120** may be formed using techniques such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, any solution printing technology, as well as thermal evaporation.

As shown, a HTL **130** is formed on the HIL **120**. In accordance with embodiments, the HTL **130** may be a common layer shared by multiple subpixels within a pixel, and may be a common layer across multiple pixels. The HTL **130** transports positive charge (holes) to the QD layer **140**, the emissive layer in the QD-LED stack, and physically separates the HIL **120** from the QD layer **140**. HTL **130** may be formed of electron rich materials such as arylamines, polyfluorene derivatives, and nanoparticle metal oxides (e.g. NiO). The HTL **130** may be formed using techniques such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, any solution printing technology, as well as thermal evaporation.

As shown, a QD layer **140** is formed on the HTL **130**. In accordance with embodiments, the QD layer **140** may be formed or patterned only in a QD-LED subpixel, or the QD layer **140** may be a common layer shared by multiple subpixels within a pixel, or may be a common layer across multiple pixels. The QD layer **140** may be formed of light emitting semiconductor nanoparticles that emit light at desired wavelength and full width at half max. Exemplary nanoparticles include spherical, rod shaped, platelet (2D quantum well) including semiconductor materials such as CdSe, InP, GaSe, etc. The QD layer **140** may be formed using techniques such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure print-

ing, and any solution printing technology. In an embodiment QD layer **140** may be formed by transfer printing an array of QD layers **140** into an array of subpixels.

As shown, an ETL **150** is formed on the QD layer **140**. In accordance with embodiments, the ETL **150** may be a common layer shared by multiple subpixels within a pixel, and may be a common layer across multiple pixels. The ETL **150** may be a high electron mobility layer that transports negative charge (electrons) into the QD layer **140** and physically separates the EIL **160** from the QD layer **140**. ETL **150** may be formed of electron deficient materials such as organometallic compounds, organic small molecules (e.g. substituted benzimidazoles), and nanoparticle metal oxides (e.g. ZnO). The ETL **150** may be formed using techniques such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, any solution printing technology, as well as thermal evaporation.

As shown, an EIL **160** is formed on the ETL **150**. In accordance with embodiments, the EIL **160** may be a common layer shared by multiple subpixels within a pixel, and may be a common layer across multiple pixels. The EIL **160** facilitates the injection of negative charge (electrons) from the electrode into the ETL **150**. EIL **160** may be formed of alkali metal salts such as LiF, low work function metals such as Ca, Ba, and n-doped material (e.g. combination of electron transport material and electron donating material). In an embodiment, the EIL **160** is formed by thermal evaporation.

As shown, a cathode **170** is formed on the EIL **160**. Cathode **170** may be formed of a variety of electrically conductive materials, including transparent or semi-transparent materials. In accordance with embodiments, the cathode **170** may be a common layer shared by multiple subpixels within a pixel, and may be a common layer across multiple pixels. In an embodiment, cathode **170** is formed of materials such as Ca/Mg, Sm/Au, Yb/Ag, Ca/Ag, Ba/Ag, and Sr/Ag. For example, in a double layer Ca/Mg the Ca layer has a low work-function for electron injection, whereas a Mg capping layer improves electrical conductance of the cathode **170**. In an embodiment, cathode **170** is formed by thermal evaporation.

Referring now to FIG. 2, an energy diagram similar to FIG. 1 is provided with the addition of a nanoparticle ETL **180** formed between the QD layer **140** and the ETL **150** in accordance with an embodiment. In an embodiment, nanoparticle ETL **180** includes an assembly of metal oxide nanoparticles, such as ZnO nanoparticles. In the embodiment illustrated, nanoparticle ETL **180** facilitates the transport of electrons from ETL **150** to the QD layer **140** and physically separates the QDs within QD layer **140** from an organic ETL **150**. In an embodiment, ETL **180** is formed using a technique such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, and any solution printing technology. In an embodiment ETL **180** may be formed by transfer printing an array of ETLs **180** into an array of subpixels. In an embodiment, transfer printing includes transferring an ETL **180**/QD layer **140** stack.

Referring now to FIG. 3, an energy diagram similar to FIG. 2 is provided with the addition of an insulating layer **185** formed between the QD layer **140** and the nanoparticle ETL **180** in accordance with an embodiment. The insulating layer **185** may function to modulate electron current into the QD layer **140**, or more specifically electron injection from the nanoparticle ETL **180** to the QD layer **140** in order to mitigate excess electron current. This modulation may be adjusted by composition and thickness of the insulating

layer **185**. In an embodiment, the insulating layer is nanometers to tens of nanometers thick. In an embodiment, insulating layer **185** is formed of poly (methyl methacrylate) (PMMA). In an embodiment, insulating layer **185** is formed using a technique such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, and any solution printing technology. In an embodiment insulating layer **185** may be formed by transfer printing an array of insulating layers **185** into an array of subpixels. In an embodiment, transfer printing includes transferring an ETL **180**/insulating layer **185**/QD layer **140** stack.

Referring now to FIG. 4, an energy diagram similar to FIG. 2 is provided with modified energy levels of the HTL **130** in accordance with an embodiment. For example, the HOMO and LUMO energy levels of the HTL **130** may be modified by the use of non-traditional deep HOMO based compounds to more closely match the QD HOMO energy level. In an embodiment, the energy difference between the HTL **130** HOMO energy level and the QD layer **140** HOMO energy level is less than 0.5 eV with the inclusion of non-traditional deep HOMO based compounds for HTL **130**. Exemplary materials include nanoparticle metal oxides (e.g. NiO), and organic based molecules (e.g. acene and carbazole derivative based compounds, carbazole derivative based polymers, polyphenylenes, derivatized triphenylenes). In an embodiment, HTL **130** is formed using any technique previously described for HTL **130**.

Referring now to FIG. 5, an energy diagram similar to FIG. 4 is provided with the addition of a metal oxide nanoparticle HTL **190** between the QD layer **140** and the HTL **130** in accordance with an embodiment. In an embodiment, metal oxide nanoparticle HTL **190** includes an assembly of metal oxide nanoparticles, such as NiO nanoparticles. In the embodiment illustrated, nanoparticle HTL **190** facilitates the transport of holes from HTL **130** to the QD layer **140** and physically separates the QDs within QD layer **140** from an organic HTL **130**. The HTL **190** may be formed using techniques such as spin coating, ink jet printing, slot die coating, nozzle printing, contact printing, gravure printing, and any solution printing technology. In an embodiment HTL **190** may be formed by transfer printing an array of HTLs **190** into an array of subpixels. In an embodiment, transfer printing includes transferring an HTL **190**/QD layer **140** stack. In an embodiment, transfer printing includes transferring an HTL **190**/QD layer **140**/ETL **180** stack. In an embodiment, transfer printing includes transferring an HTL **190**/QD layer **140**/insulating layer **185**/ETL **180** stack.

Referring now to FIGS. 6-9 various hybrid pixel layouts are provided to illustrate the integration of QD-LED and OLED subpixels within a display. In particular, the illustrated hybrid pixel layouts are based upon the QD-LED stack structures illustrated and described with regard to FIGS. 1, 2 and 4. However, these illustrations are exemplary and may include additional layers, such as insulating layer **185** and HTL **190**. Accordingly, the implementation of insulating layer **185** and HTL **190** is not limited to the embodiments illustrated and described with regard to FIGS. 3 and 5.

In the case of electroluminescent displays, the red, green, and blue subpixels within a single display pixel are comprised of an assembly of layers common to all three subpixels and layers specific to a particular subpixel. In accordance with some embodiments, the common layers in the hybrid pixel may include the HIL **120**, HTL **130**, and ETL **150**, EIL **160**, and cathode **170** layer. In some embodiments, the layers specific to each subpixel may include the buffer transport layers (BTLs) **210** and the emissive layers (e.g.

organic emission layers **200-R**, **200-G**, and QD layer **140**). In some embodiment, the BTL **210** and/or QD layer **140** may be common layers. The thickness of the common layers and BTLs **210** are selected to ensure specific micro cavity design for each of the red, green, and blue subpixels. In the hybrid pixel assembly, the BTLs **210** have two roles- one is to further adjust the cavity strength as well as to ensure that the layer next to the emissive layer has a band gap higher than that of the emissive species itself. In the case of the red and green phosphorescent organic emission layers **200-R**, **200-G**, the BTL **210** should have a triplet energy that is higher than the triplet energy of the emitter material. Furthermore, the BTL **210** energy levels (HOMO, LUMO) may be selected to facilitate hole or electron blocking functionality next to the emissive layer.

FIG. 6 is a schematic cross-sectional side view illustration of a hybrid pixel including a patterned QD layer **140** in accordance with an embodiment. In the embodiment illustrated, separate anodes **110-R**, **110-G**, **110-B** are provided for each separate subpixel (e.g. RGB). A common HIL **120** and common HTL **130** are formed over the separate anodes **110-R**, **110-G**, **110-B**.

In the particular embodiment illustrated in FIG. 6, the blue-emitting QD-LED subpixel includes a QD layer **140** formed on the common HTL **130**, and a nanoparticle ETL **180** (e.g. ZnO nanoparticles) formed on the QD layer **140**. In one embodiment, the QD layer **140** and nanoparticle ETL **180** are formed using any of the previously described solution-based techniques. In another embodiment, the QD layer **140** and nanoparticle ETL **180** are transfer printed either separately, or together as a layer stack. Following the formation of the QD layer **140** and nanoparticle ETL **180**, the remainder of the layers may be fabricated, for example, by thermal evaporation.

Still referring to FIG. 6, buffer transport layers **210-R**, **210-G** are formed on the common HTL **130**, followed by the formation of red and green emitting organic emission layers **200-R**, **200-G** on the BTLs **210-R**, **210-G**. In the arrangement illustrated in FIG. 6, **210-R**, **210-G** are BTLs in the red and green OLED subpixels, and are both serving as electron blocking layers. Exemplary materials may include carbazole and triphenylene based organic compounds, which may be formed by thermal evaporation. A common ETL **150** may then be formed on the organic emission layers **200-R**, **200-G**, and the nanoparticle ETL **180**. A common EIL **160** may then be formed over the common ETL **150**, followed by the formation of a common cathode **170** layer.

As shown in FIG. 6, the hybrid pixel arrangement includes a QD-LED stack structure similar to that illustrated in FIG. 2 or FIG. 4. In other embodiments, the hybrid pixel arrangement may optionally include an insulating layer **185**, and/or HTL **190** as previously described with regard to FIGS. 3 and 5. Additionally, the nanoparticle ETL **180** may optionally be removed.

Referring now to FIGS. 7-9 additional hybrid pixel arrangements are illustrated including a common QD layer **140** in accordance with embodiments. In such arrangements, additional processing operations associated with patterning the QD layer **140** may be removed, which may reduce time of production. This may additionally eliminate resolution (e.g. pixels per inch) constraints related to patterning or printing.

FIG. 7 is a schematic cross-sectional side view illustration of a hybrid pixel similar to FIG. 6, with common QD layer **140**, and no nanoparticle ETL **180**. Additionally, the optional BTLs **210-R**, **210-G** are removed. In the embodiment illustrated, the common ETL **150** is formed on organic emission

layers **200-R**, **200-G** in the OLED subpixels, and on the common QD layer **140** in the QD-LED subpixel.

FIG. **8** is a schematic cross-sectional side view illustration of a hybrid pixel similar to FIG. **6**, with common QD layer **140**, and common nanoparticle ETL **180** formed on the common QD layer **140**. In the embodiment illustrated, the common ETL **150** is formed on organic emission layers **200-R**, **200-G** in the OLED subpixels, and on the common nanoparticle ETL **180** in the QD-LED subpixel.

FIG. **9** is a schematic cross-sectional side view illustration of a hybrid pixel similar to FIG. **7**, with BTLs **210-R**, **210-G** formed on the organic emission layers **200-R**, **200-G**, respectively. The BTLs **210-R**, **210-G** in FIG. **9** are distinguishable from the BTLs illustrated in FIGS. **6** and **8**, in that the BTLs **210-R**, **210-G** in FIG. **9** serve as hole blocking layers as opposed to electron blocking layers. Exemplary materials for BTLs serving as hole blocking layers may include organometallic wide band gap compounds (hole blocking) and other organic compounds (e.g. substituted benzimidazoles), which may be formed by thermal evaporation.

FIG. **10** is a schematic cross-sectional side view illustration of a hybrid pixel similar to FIG. **9**, with a common BTL **210** being formed on the organic emission layers **200-R**, **200-G** and common QD layer **140**, as opposed to separate BTLs being formed in each OLED subpixel.

In other embodiments, the hybrid pixel arrangements illustrated in FIGS. **7-9** may optionally include a common insulating layer **185**, and/or common HTL **190** as previously described with regard to FIGS. **3** and **5**.

FIG. **11** is a schematic cross-sectional side view illustration of an inverted hybrid pixel including a common QD layer **140** in accordance with an embodiment. In the embodiment illustrated, separate cathodes **170-R**, **170-G**, **170-B** are provided for each separate subpixel (e.g. RGB). In an embodiment, the cathodes **170-R**, **170-G**, **170-B** are formed of ITO. A common nanoparticle ETL **180** is formed over the separate cathodes **170-R**, **170-G**, **170-B**, followed by the formation of a common QD layer **140** over the common nanoparticle ETL **180**. Similar to the arrangements illustrated in FIGS. **7-10**, the arrangement in FIG. **11** may eliminate the resolution constraints associated with patterning or printing. Still referring to FIG. **11**, organic emission layers **200-R**, **200-G** are formed on the QD layer **140**, followed by the formation of BTLs **210-R**, **210-G** on the organic emission layers **200-R**, **200-G**, respectively, for example using thermal evaporation. A common HTL **130** is then formed on the BTLs **210-R**, **210-G** in the OLED subpixels, and the common QD layer **140** in the QD-LED subpixel. A common HIL **192** may then be formed over the common HTL **130**, for example, using thermal evaporation. Exemplary materials of HIL **192** include hexaazatriphenylene-hexacarbonitrile (HAT-CN) or molybdenum oxide (MoOx). A common anode **110** layer is then formed over the common HIL **192**. In an embodiment, the common anode **110** layer is formed of aluminum.

Referring now to FIGS. **12-18** various configurations of hybrid pixels including tandem structure stacks are provided in accordance with embodiments, in which multiple emitting units are stacked vertically. Referring to FIG. **12**, a QD layer **140**, HTL **130**, HIL **120** may be formed over separate anodes **110-R**, **110-G**, **110-B** similarly as previously described with regard to FIG. **7**, followed by the formation of a common ETL **150** over the common QD layer **140** in the OLED subpixels and the QD-LED subpixel. A separate cathode **170-B** may then be formed on the common ETL **150** in the QD-LED subpixel, while a semi-common charge generation

layer (CGL) **220** is formed on the common ETL **150** in the OLED subpixels. As illustrated, the semi-common CGL **220** is common to the OLED subpixels only.

In accordance with embodiments, the CGL **220** is used to connect an assembly of two emissive layers in tandem with each other. It provides positive (hole) current to the upper (with reference to the figures) emissive layers (e.g. **200-R**, **200-G**) and negative (electron) current to the lower emissive layer (e.g. QD layer **140**). Typically a CGL **220** is comprised of two distinct layers. For example, the electron current can be provided by a layer comprised of alkali metal salts such as LiF, low work function metals such as Ca, Ba, and n-doped material (e.g. combination of electron transport material and electron donating material). The hole current can be provided by a layer comprised of combination of arylamine based hole transport host and electron accepting dopant (e.g. charge transfer salts), strongly electron accepting small organic molecules, metal oxides. In accordance with embodiments, CGL **220** is formed by thermal evaporation.

A semi-common HIL **120** may then be formed on the semi-common CGL **220**, followed by the formation of a semi-common HTL **130** on the semi-common HIL **120**. Organic emission layers **200-R**, **200-G** may then be formed on the semi-common HTL **130** in separated OLED subpixels. A semi-common ETL **150** may then be formed over both organic emission layers **200-R**, **200-G**, followed by the formation of a semi-common EIL **160**, and a semi-common cathode **170** in both OLED subpixels. A red color filter **230-R** may optionally be formed over the semi-common cathode **170** in the red emitting OLED subpixel, and a green color filter **230-G** may optionally be formed over the semi-common cathode **170** in the green emitting OLED subpixel.

FIG. **13** is a schematic cross-sectional side view illustration of a hybrid pixel including a tandem structure stack similar to that provided in FIG. **12** with one difference being the substitution of nanoparticle ETL **180** in place of ETL **150**. Additionally, nanoparticle ETL **180** may be fabricated using a solution-based technique.

FIG. **14** is a schematic cross-sectional side view illustration of a hybrid pixel including a tandem structure stack similar to that provided in FIG. **13** with one difference being the addition of semi-common ETL **150** between the semi-common CGL **220** and the semi-common HIL **120**.

Referring now to FIG. **15** a schematic cross-sectional side view illustration of a hybrid pixel including a tandem structure stack is provided in accordance with an embodiment in which the QD-LED subpixel is inverted. As shown, a common nanoparticle ETL **180** may be formed over separate anodes **110-R**, **110-G**, and cathode **170-B**. In an embodiment, anodes **110-R**, **110-G**, and cathode **170-B** are formed of the same material, such as ITO. A common QD layer **140** may then be formed over the common nanoparticle ETL **180**. The common nanoparticle ETL **180** and common QD layer **140** may be formed using solution-based techniques. A common HTL **130** may then be formed over the common QD layer **140**, followed by the formation of a common HIL **192** over the common HTL **130**, for example by thermal evaporation. An anode **110-B** may then be formed on the common HIL **192** in the QD-LED subpixel, while a semi-common HTL **130** is formed on the common HIL **192** in the OLED subpixels.

BTLs **210-R**, **210-G** are then formed on the semi-common HTL **130** in the red-emitting and green-emitting OLED subpixels, followed by the formation of organic emission layers **200-R**, **200-G** on the BTLs **210-R**, **210-G**. In the arrangement illustrated in FIG. **15**, **210-R**, **210-G** are BTLs

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in the red and green OLED subpixels, and are both serving as electron blocking layers. Exemplary materials may include carbazole and triphenylene based organic compounds, which may be formed by thermal evaporation. A semi-common ETL **150** is then formed over the organic emission layers **200-R**, **200-G**, followed by the formation of a semi-common EIL **160** on the semi-common ETL **150**, and a semi-common cathode **170** on the semi-common EIL **160**.

Referring now to FIGS. **16-18**, schematic cross-sectional side view illustrations of hybrid pixels including tandem structure stacks are provided similar to those in FIGS. **12-14** with one difference being that a separate cathode **170** is not provided for the QD-LED subpixel, and the previously described and illustrated semi-common layers are now common layers across both the OLED subpixels and the QD-LED subpixel. Additionally, a blue color filter **230-B** may be formed over the common cathode **170** layer in the QD-LED subpixel.

FIGS. **19-20** are schematic cross-sectional side view illustrations blended emission tandem structure stacks in accordance with embodiments. As such, the structures illustrated in FIGS. **19-20** may be utilized to emit a blended spectrum, such as white light. As illustrated in FIGS. **19-20**, each layer may be a common layer formed on top of another common layer. In both embodiments illustrated in FIGS. **19-20**, the ETL **150** formed above the solution-based layers may be substituted with a solution-based nanoparticle ETL **180**, or ETL **150** may be formed on top of a solution-based nanoparticle ETL **180**.

In utilizing the various aspects of the embodiments, it would become apparent to one skilled in the art that combinations or variations of the above embodiments are possible for forming hybrid OLED/QD-LED pixels. Although the embodiments have been described in language specific to structural features and/or methodological acts, it is to be understood that the appended claims are not necessarily limited to the specific features or acts described. The specific features and acts disclosed are instead to be understood as embodiments of the claims useful for illustration.

What is claimed is:

1. A display comprising:

a tandem hybrid pixel including an organic light emitting diode (OLED) subpixel and a quantum dot light emitting diode (QD-LED) subpixel;

a common hole transport layer in the OLED subpixel and the QD-LED subpixel;

a common quantum dot layer over the common hole transport layer in the QD-LED subpixel and in the OLED subpixel;

a semi-common charge generation layer over the common quantum dot layer in the OLED subpixel;

a first cathode over the common quantum dot layer in the QD-LED subpixel;

a semi-common hole transport layer over the semi-common charge generation layer in the OLED subpixel;

an organic emission layer over the semi-common hole transport layer in the OLED subpixel;

a semi-common electron transport layer over the organic emission layer in the OLED subpixel; and

a semi-common second cathode over the semi-common electron transport layer in the OLED subpixel.

2. The display of claim **1**, further comprising:

a common nanoparticle electron transport layer comprising metal-oxide nanoparticles over the common quantum dot layer in the QD-LED subpixel and in the OLED subpixel;

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wherein the semi-common charge generation layer is over the common nanoparticle electron transport layer in the OLED subpixel, and the first cathode is over the common nanoparticle electron transport layer in the QD-LED subpixel.

3. The display of claim **1**, wherein the organic emission layer is over the common quantum dot layer in the OLED subpixel.

4. The display of claim **1**, further comprising a first anode under the common hole transport layer in the QD-LED subpixel, and a second anode under the common hole transport layer in the OLED subpixel.

5. The display of claim **1**, wherein the organic emission layer comprises a phosphorescent material.

6. A display comprising:

a tandem hybrid pixel including an organic light emitting diode (OLED) subpixel and a quantum dot light emitting diode (QD-LED) subpixel;

a common hole transport layer in the OLED subpixel and the QD-LED subpixel;

a common quantum dot layer over the common hole transport layer in the QD-LED subpixel and in the OLED subpixel;

a common charge generation layer over the common quantum dot layer in the OLED subpixel and in the QD-LED subpixel;

a second common hole transport layer over the common charge generation layer in the OLED subpixel and in the QD-LED subpixel;

an organic emission layer over the second common hole transport layer in the OLED subpixel;

a common electron transport layer over the second common hole transport layer in the OLED subpixel and in the QD-LED subpixel, the common electron transport layer additionally over the organic emission layer in the OLED subpixel; and

a common cathode over the common electron transport layer in the OLED subpixel and in the QD-LED subpixel.

7. The display of claim **6**, further comprising:

a common nanoparticle electron transport layer comprising metal-oxide nanoparticles over the common quantum dot layer in the QD-LED subpixel and in the OLED subpixel;

wherein the common charge generation layer is over the common nanoparticle electron transport layer in the OLED subpixel and in the QD-LED subpixel.

8. The display of claim **6**, wherein the organic emission layer is over the common quantum dot layer in the OLED subpixel.

9. The display of claim **6**, further comprising a first anode under the common hole transport layer in the QD-LED subpixel, and a second anode under the common hole transport layer in the OLED subpixel.

10. The display of claim **6**, wherein the organic emission layer comprises a phosphorescent material.

11. A display with tandem QD-LED and OLED tandem stack comprising:

a common anode;

a common hole transport layer over the common anode;

a common quantum dot layer over the common hole transport layer;

a common charge generation layer over the common quantum dot layer;

a second common hole transport layer over the common charge generation layer;

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a common organic emission layer over the second common hole transport layer;
a common electron transport layer over the common organic emission layer; and
a common cathode over the common electron transport layer. 5

12. The display of claim **11**, further comprising a second common organic emission layer between the common organic emission layer and the common electron transport layer. 10

13. The display of claim **12**, further comprising:
a second common electron transport layer over the common organic emission layer;
a second charge generation layer over the second common electron transport layer; and 15
a third common hole transport layer over the second charge generation layer;
wherein the second common organic emission layer is over the third common hole transport layer.

14. The display of claim **11**, further comprising a second common electron transport layer between the common quantum dot layer and the common charge generation layer. 20

15. The display of claim **14**, wherein the second common electron transport layer comprises metal-oxide nanoparticles. 25

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专利名称(译)	量子点LED和OLED集成以实现高效显示		
公开(公告)号	US10461131	公开(公告)日	2019-10-29
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[标]申请(专利权)人(译)	苹果公司		
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CPC分类号	H01L51/5278 H01L27/3209 H01L27/3211 H01L51/5044 H01L51/5072 H01L51/502 H01L2251/5369 H01L51/0013 H01L51/5016 H01L51/0003		
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摘要(译)

描述了包括包括OLED子像素和QD-LED子像素的混合像素的显示器。在一个实施例中，OLED和QD-LED叠层被集成到同一像素中，OLED和QD-LED叠层共享多个公共层。

